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DUAL N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)max}	I _D T _A = +25°C
20V	15.5mΩ @ V_{GS} = 4.5 V	7.5A
	16.5mΩ @ V_{GS} = 4.0V	7.3A
	19mΩ @ V_{GS} = 3.1 V	6.9A
	$20m\Omega$ @ $V_{GS} = 2.5V$	6.7A
	$30m\Omega$ @ V_{GS} = 1.8 V	5.4A

Description

This new generation MOSFET has been designed to minimize the onstate resistance $(R_{DS(ON)})$ and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

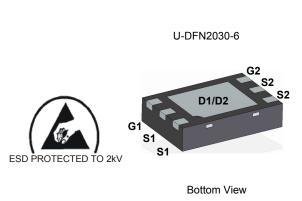
- Power Management Functions
- Battery Pack
- Load Switch

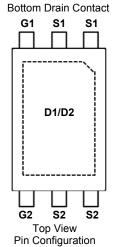
Features

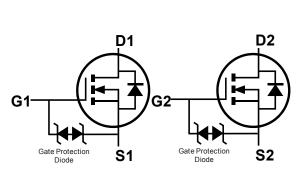
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: U-DFN2030-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper leadframe. Solderable per MIL-STD-202, Method 208 (4)
- Weight: 0.012 grams (approximate)







Ordering Information (Note 4)

Part Number	Case	Packaging
DMN2016LHAB-7	U-DFN2030-6	3,000 / Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



26W = Product Type Marking Code YYWW = Date Code Marking YY = Last digit of year (ex: 12 for 2012) WW = Week code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characte	Symbol	Value	Unit		
Drain-Source Voltage	V_{DSS}	20	V		
Gate-Source Voltage	V_{GSS}	±12	V		
Continuous Dusin Comment (Nata CVV - 4.5V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	7.5 5.8	Α
Continuous Drain Current (Note 6) V _{GS} = 4.5V	t < 10s	T _A = +25°C T _A = +70°C	I _D	7.7 6.0	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	45	Α

Thermal Characteristics

Characteristic	Symbol	Value	Units		
Total Dawar Dissination (Note 5)	T _A = +25°C	7	1.2	W	
Total Power Dissipation (Note 5)	T _A = +70°C	P_D	0.75	VV	
Thermal Decistance Junction to Ambient (Note 5)	Steady State	0	106	°C/W	
Thermal Resistance, Junction to Ambient (Note 5)	t < 10s	$R_{\theta JA}$	100	C/VV	
Total Dawar Dissination (Note 6)	T _A = +25°C	7	1.65	W	
Total Power Dissipation (Note 6)	T _A = +70°C	P_{D}	1	VV	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	ם	78		
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	72	°C/W	
Thermal Resistance, Junction to Case	$R_{ heta JC}$	11.4			
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C	

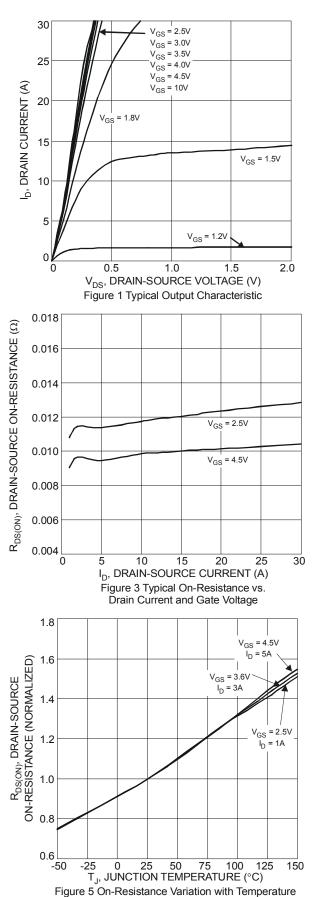
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

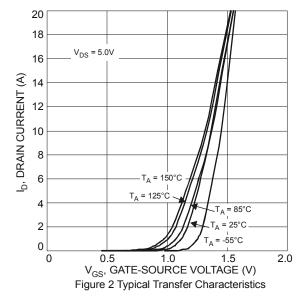
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	20			V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}		_	1.0	μΑ	$V_{DS} = 20V, V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	_	_	±10	μΑ	$V_{GS} = \pm 8V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)			-	_	_		
Gate Threshold Voltage	V _{GS(th)}	0.5	0.71	1.1	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
			13	15.5	mΩ	$V_{GS} = 4.5V, I_D = 4.0A$	
			13.5	16.5		$V_{GS} = 4.0V, I_D = 4.0A$	
Static Drain-Source On-Resistance	R _{DS(ON)}	_	14	19		$V_{GS} = 3.1V, I_D = 4.0A$	
			15	20		$V_{GS} = 2.5V, I_D = 4.0A$	
			21	30		$V_{GS} = 1.8V, I_D = 3.5A$	
Forward Transfer Admittance	Y _{fs}	1	25	_	S	$V_{DS} = 5V, I_{D} = 6A$	
Diode Forward Voltage	V_{SD}	_	0.75	1.0	V	$V_{GS} = 0V$, $I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	C _{iss}	_	1550	_	pF		
Output Capacitance	Coss	_	166	_	pF	$V_{DS} = 10V, V_{GS} = 0V,$ - f = 1.0MHz	
Reverse Transfer Capacitance	Crss	_	145	_	pF	1 - 1.0WHZ	
Gate Resistance	R_g	_	1.37	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 2.5V)	Q_g	_	8.4	_	nC		
Total Gate Charge (V _{GS} = 4.5V)	Q_g	_	16	_	nC	V _{DS} = 10V, I _D = 6A	
Gate-Source Charge	Q_{gs}	_	2.3	_	nC		
Gate-Drain Charge	Q_{gd}	1	2.5	_	nC		
Turn-On Delay Time	t _{D(on)}	_	6.9	_	ns		
Turn-On Rise Time	t _r	_	15.5	_	ns	$V_{DD} = 10V, R_{L} = 1.7\Omega,$ $V_{GS} = 5.0V, R_{G} = 3\Omega$	
Turn-Off Delay Time	t _{D(off)}	_	40.9	_	ns		
Turn-Off Fall Time	t _f		12	_	ns		

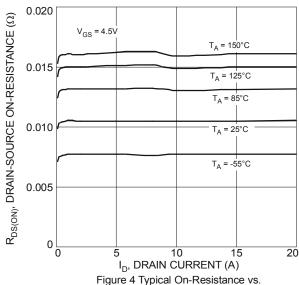
Notes:

- 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout
- Device mounted on FR-4 substrate PC board, 2oz copper, with 1 inch square copper pad
 Repetitive rating, pulse width limited by junction temperature
 Guaranteed by design. Not subject to product testing





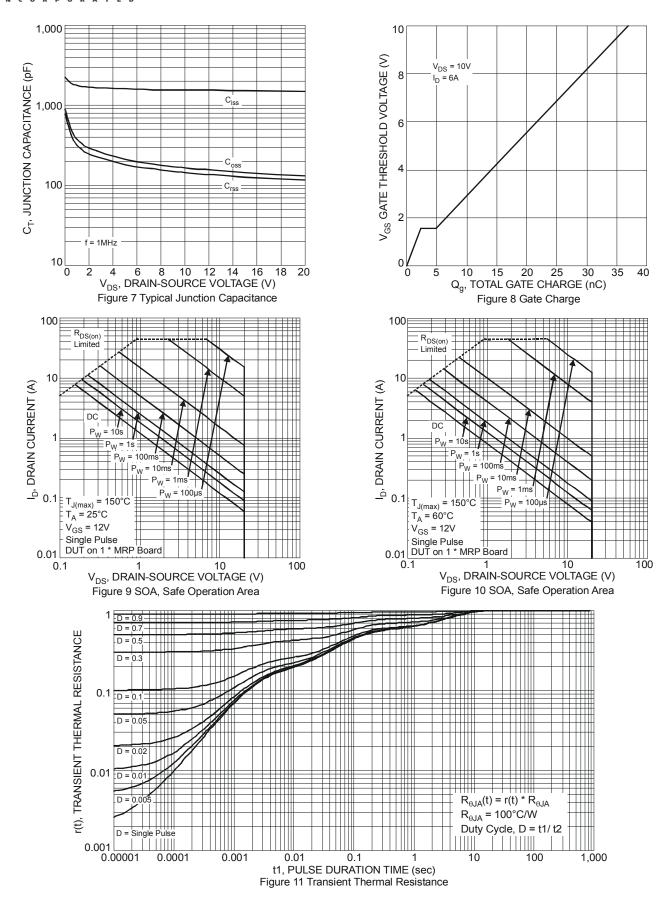




0.020 $R_{DS(ON)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 0.018 $V_{GS} = 2.5V$ I_D = 1A 0.016 V_{GS} = 3.6V 0.014 I_D = 3A 0.012 V_{GS} = 4.5V I_D = 5A 0.010 0.008 0.006 0.004 100 25 50 75 T_J, JUNCTION TEMPERATURE (°C) Figure 6 On-Resistance Variation with Temperature

Drain Current and Temperature

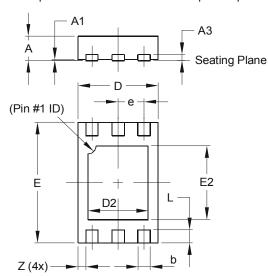






Package Outline Dimensions

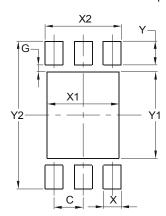
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



U-DFN2030-6						
Type B						
Dim	Dim Min Max					
Α	0.55	0.65	0.60			
A1	0	0.05	0.02			
A3	-	-	0.15			
b	0.25	0.35	0.30			
D	1.95	2.05	2.00			
D2	1.40	1.60	1.50			
Е	2.95	3.05	3.00			
E2	1.74	1.94	1.84			
е	-	-	0.65			
L	0.28	0.38	0.33			
Ζ	1	-	0.20			
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value			
Illiensions	(in mm)			
C	0.650			
G	0.150			
Х	0.400			
X1	1.600			
X2	1.700			
Y	0.530			
Y1	1.940			
Y2	3.300			



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